

PSMN5R0-80BS

N-channel 80 V, 5.1 m Ω standard level MOSFET in D2PAK Rev. 1 — 20 March 2012

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	270	W
Tj	junction temperature			-55	-	175	°C
Static char	acteristics						
R _{DSon} drain-source on-state resista	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 °C;$ see <u>Figure 13</u> ; see <u>Figure 12</u>		-	7.19	8.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12		-	4.36	5.1	mΩ
Dynamic c	haracteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 40 \text{ V};$		-	21	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15		-	101	-	nC
Avalanche	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_{D} = 100 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; unclamped		-	-	396	mJ

^[1] Continuous current is limited by package



2. Pinning information

Table 2. Pinning information

		,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R0-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN5R0-80BS	PSMN5R0-80BS

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		, ,				
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	80	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	[1]	-	100	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	598	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	270	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	ain diode					
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	598	Α
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω ; unclamped		-	396	mJ

[1] Continuous current is limited by package

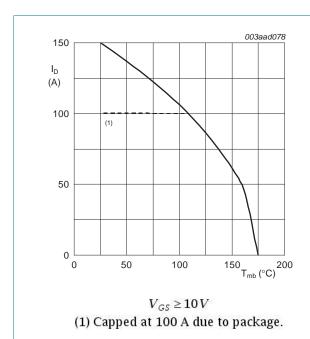
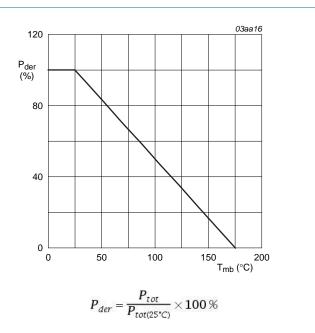


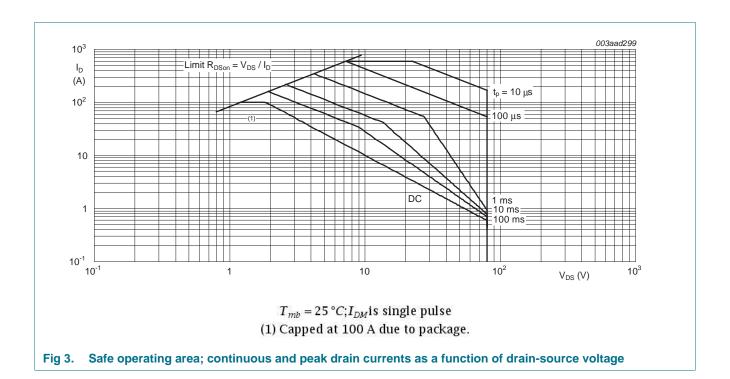
Fig 1. Continuous drain current as a function of mounting base temperature



ig 2. Normalized total power dissipation as a function of mounting base temperature

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	0.3	0.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

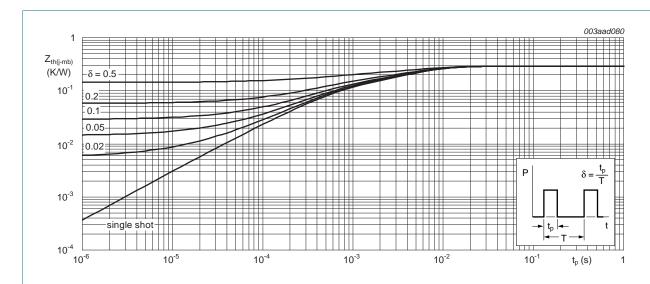


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	73	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.6	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see Figure 11; see Figure 10	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	8	μΑ
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	150	μΑ
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	10.46	12.3	Ω
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see Figure 13; see Figure 12	-	7.19	8.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	4.36	5.1	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.95	-	Ω
Dynamic c	haracteristics					
Q _{G(tot)} total gate charge		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	87	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	101	-	nC
Q_GS	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	26	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	18	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	8	-	nC
Q_{GD}	gate-drain charge		-	21	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 40 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.2	-	V
C _{iss}	input capacitance	V _{DS} = 40 V; V _{GS} = 0 V; f = 1 MHz;	-	6793	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	913	-	pF
C _{rss}	reverse transfer capacitance		-	350	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 10 \text{ V};$	-	33	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	21	-	ns
t _{d(off)}	turn-off delay time		-	73	-	ns
t _f	fall time		-	14	-	ns

116

nC

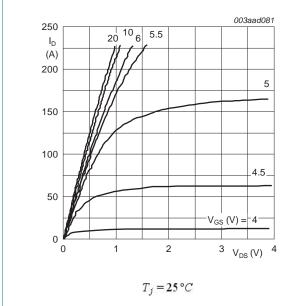
 Q_{r}

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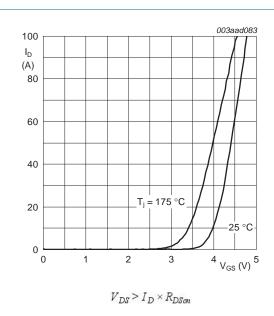
Characteristics ... continued Table 7. Tested to JEDEC standards where applicable.

recovered charge

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	ain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$;	-	56	-	ns
0	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$	_	116	_	nC



Output characteristics: drain current as a Fig 5. function of drain-source voltage; typical values



Transfer characteristics: drain current as a Fig 6. function of gate-source voltage; typical values

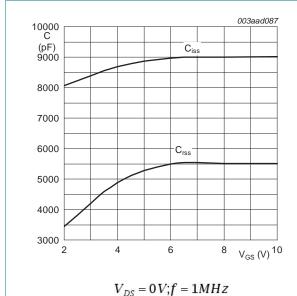
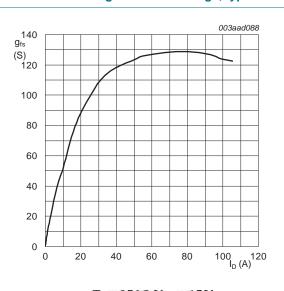


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25 \,{}^{\circ}C; V_{DS} = 15 \, V$

Fig 8. Forward transconductance as a function of drain current; typical values

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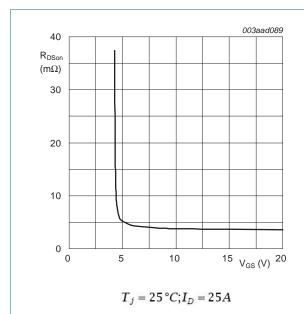


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

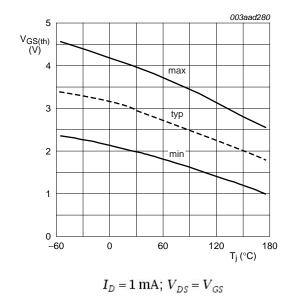


Fig 10. Gate-source threshold voltage as a function of junction temperature

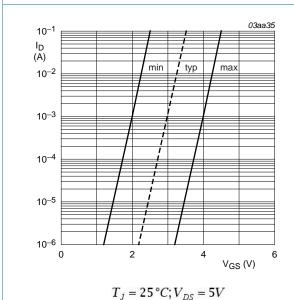


Fig 11. Sub-threshold drain current as a function of gate-source voltage

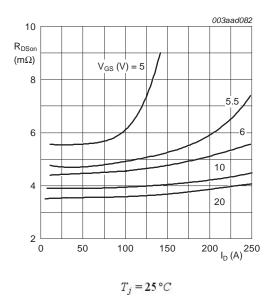


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

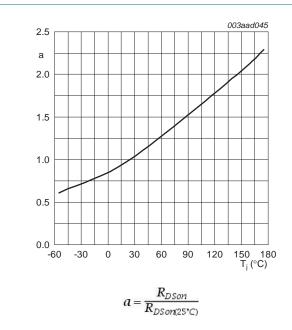


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

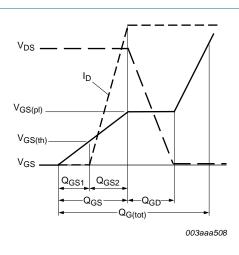
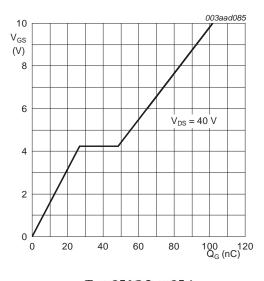
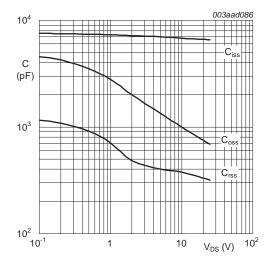


Fig 14. Gate charge waveform definitions



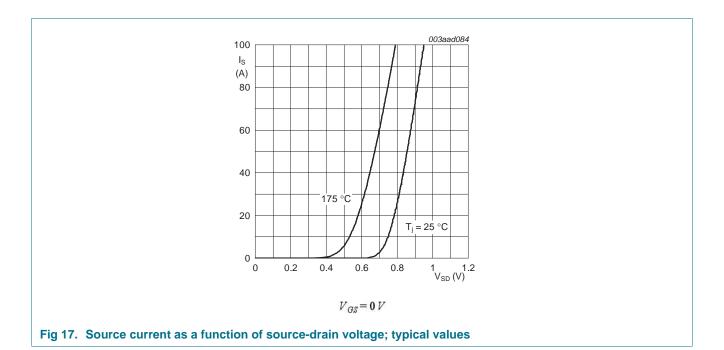
 $T_j = 25\,^{\circ}C; I_D = 25A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0V; f = 1MHz$$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



8. Package outline

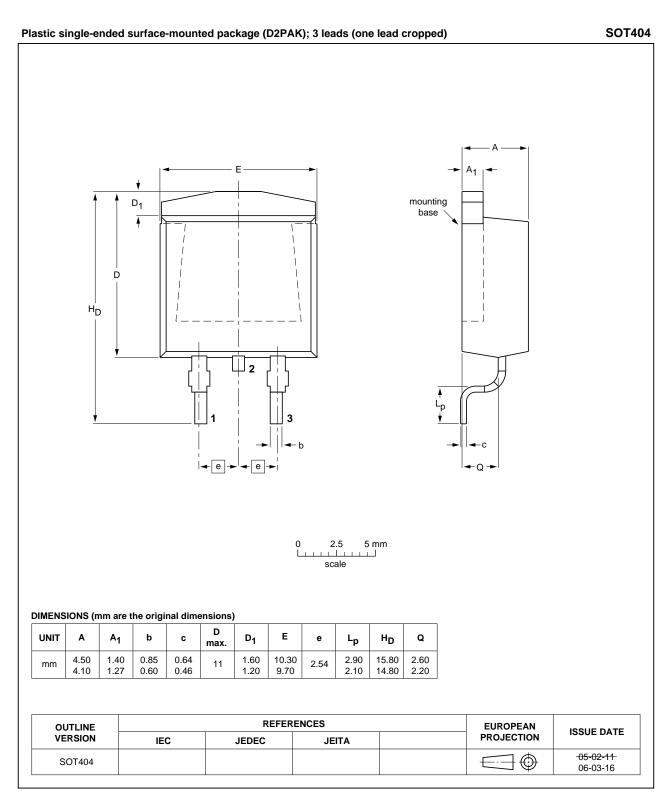


Fig 18. Package outline SOT404 (D2PAK)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN5R0-80BS v.1	20120320	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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